

P4C168, P4C169, P4C170 ULTRA HIGH SPEED 4K x 4 STATIC CMOS RAMS

FEATURES

- Full CMOS, 6T Cell
- High Speed (Equal Access and Cycle Times)
 - 12/15/20/25/35ns (Commercial)
 - 20/25/35/45/55/70ns (P4C168 Military)
- Low Power Operation (Commercial)
 - 715 mW Active
 - 193 mW Standby (TTL Input) P4C168
 - 83 mW Standby (CMOS Input) P4C168
- Single 5V±10% Power Supply
- Fully TTL Compatible, Common I/O Ports
- Three Options
 - P4C168 Low Power Standby Mode
 - P4C169 Fast Chip Select Control
 - P4C170 Fast Chip Select, Output Enable Controls
- Standard Pinout (JEDEC Approved)
 - P4C168: 20-pin DIP, SOJ, LCC, SOIC, CERPACK, and Flat Pack
 - P4C169: 20-pin DIP and SOIC
 - P4C170: 22-pin DIP

DESCRIPTION

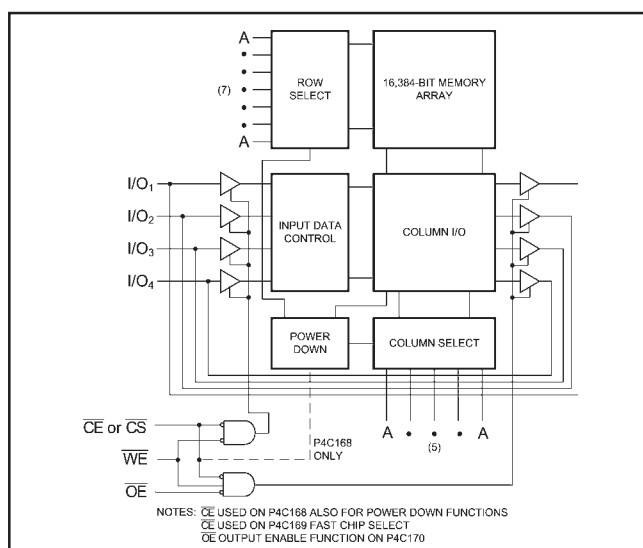
The P4C168, P4C169 and P4C170 are a family of 16,384-bit ultra high-speed static RAMs organized as 4K x 4. All three devices have common input/output ports. The P4C168 enters the standby mode when the chip enable (\overline{CE}) control goes HIGH; with CMOS input levels, power consumption is only 83mW in this mode. Both the P4C169 and the P4C170 offer a fast chip select access time that is only 67% of the address access time. In addition, the P4C170 includes an output enable (\overline{OE}) control to eliminate data bus contention. The RAMs operate from a single 5V ± 10% tolerance power supply.

Access times as fast as 12 nanoseconds are available, permitting greatly enhanced system operating speeds. CMOS is used to reduce power consumption to a low 715 mW active, 193 mW standby.

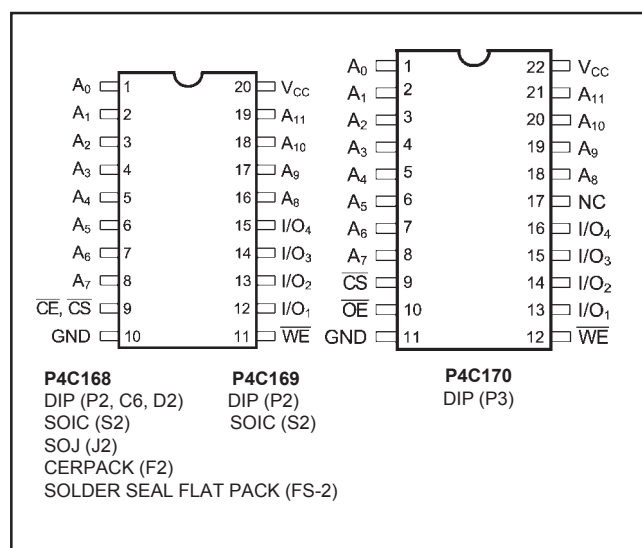
The P4C168 and P4C169 are available in 20-pin (P4C170 in 22-pin) 300 mil DIP packages providing excellent board level densities. The P4C168 is also available in 20-pin 300 mil SOIC, SOJ, CERPACK, and Flat Pack packages.

The P4C169 is also available in a 20-pin 300 mil SOIC package.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATIONS



**MAXIMUM RATINGS⁽¹⁾**

| Symbol | Parameter | Value | Unit |
|------------|---|------------------------|------|
| V_{CC} | Power Supply Pin with Respect to GND | -0.5 to +7 | V |
| V_{TERM} | Terminal Voltage with Respect to GND (up to 7.0V) | -0.5 to $V_{CC} + 0.5$ | V |
| T_A | Operating Temperature | -55 to +125 | °C |

| Symbol | Parameter | Value | Unit |
|------------|------------------------|-------------|------|
| T_{BIAS} | Temperature Under Bias | -55 to +125 | °C |
| T_{STG} | Storage Temperature | -65 to +150 | °C |
| P_T | Power Dissipation | 1.0 | W |
| I_{OUT} | DC Output Current | 50 | mA |

RECOMMENDED OPERATING CONDITIONS

| Grade ⁽²⁾ | Ambient Temp | Gnd | V_{CC} |
|----------------------|-----------------|-----|------------|
| Commercial | 0°C to 70°C | 0V | 5.0V ± 10% |
| Military | -55°C to +125°C | 0V | 5.0V ± 10% |

CAPACITANCES⁽⁴⁾ $(V_{CC} = 5.0V, T_A = 25^\circ C, f = 1.0MHz)$

| Symbol | Parameter | Conditions | Typ. | Unit |
|-----------|--------------------|----------------|------|------|
| C_{IN} | Input Capacitance | $V_{IN} = 0V$ | 5 | pF |
| C_{OUT} | Output Capacitance | $V_{OUT} = 0V$ | 7 | pF |

DC ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Test Conditions | P4C168/169/170 | | Unit |
|-----------|--|---|-----------------------------|----------------|------|
| | | | Min | Max | |
| V_{IH} | Input High Voltage | | 2.2 | $V_{CC} + 0.5$ | V |
| V_{IL} | Input Low Voltage | | -0.5(3) | 0.8 | V |
| V_{HC} | CMOS Input High Voltage | | $V_{CC} - 0.2$ | $V_{CC} + 0.5$ | V |
| V_{LC} | CMOS Input Low Voltage | | -0.5(3) | 0.2 | V |
| V_{CD} | Input Clamp Diode Voltage | $V_{CC} = \text{Min.}, I_{IN} = -18 \text{ mA}$ | | -1.2 | V |
| V_{OL} | Output Low Voltage (TTL Load) | $I_{OL} = +8 \text{ mA}, V_{CC} = \text{Min.}$ | | 0.4 | V |
| V_{OLC} | Output Low Voltage (CMOS Load) | $I_{OLC} = +100 \mu A, V_{CC} = \text{Min.}$ | | 0.2 | V |
| V_{OH} | Output High Voltage (TTL Load) | $I_{OH} = -4 \text{ mA}, V_{CC} = \text{Min.}$ | 2.4 | | V |
| V_{OHC} | Output High Voltage (CMOS Load) | $I_{OHC} = -100 \mu A, V_{CC} = \text{Min.}$ | $V_{CC} - 0.2$ | | V |
| I_{LI} | Input Leakage Current | $V_{CC} = \text{Max.}, V_{IN} = \text{GND to } V_{CC}$ | Mil. Comm'l -10 -5 | +10 +5 | μA |
| I_{LO} | Output Leakage Current | $V_{CC} = \text{Max.}, \overline{CS} = V_{IH}, V_{OUT} = \text{GND to } V_{CC}$ | Mil. Comm'l -10 -5 | +10 +5 | μA |
| I_{CC} | Dynamic Operating Current | $V_{CC} = \text{Max.}, f = \text{Max.}, \text{Outputs Open}$ | — | 130 | mA |
| I_{SB} | Standby Power Supply Current (TTL Input Levels) P4C168 only | $\overline{CE} \geq V_{IH}, V_{CC} = \text{Max.}, f = \text{Max.}, \text{Outputs Open}$ | — | 35 | mA |
| I_{SB1} | Standby Power Supply Current (CMOS Input Levels) P4C168 only | $\overline{CE} \geq V_{HC}, V_{CC} = \text{Max.}, f = 0, V_{IN} \leq V_{LC} \text{ or } V_{IN} \geq V_{HC}$ | — | 15 | mA |

AC CHARACTERISTICS—READ CYCLE $(V_{CC} = 5V \pm 10\%$, All Temperature Ranges)⁽²⁾

| Sym | Parameter | -12 | | -15 | | -20 | | -25 | | -35 | | Unit |
|-------------------------------|------------------------------------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | |
| t _{RC} | Read Cycle Time | 12 | | 15 | | 20 | | 25 | | 35 | | ns |
| t _{AA} | Address Access Time | | 12 | | 15 | | 20 | | 25 | | 35 | ns |
| t _{AC} [§] | Chip Enable Access Time | | 12 | | 15 | | 20 | | 25 | | 35 | ns |
| t _{AC} [‡] | Chip Select Access Time | | 8 | | 9 | | 12 | | 15 | | 20 | ns |
| t _{OH} | Output Hold from Address Change | 2 | | 2 | | 2 | | 2 | | 2 | | ns |
| t _{LZ} [‡] | Chip Enable to Output in Low Z | 2 | | 2 | | 2 | | 2 | | 2 | | ns |
| t _{HZ} [†] | Chip Disable to Output in High Z | | 7 | | 8 | | 9 | | 10 | | 15 | ns |
| t _{OE} [†] | Output Enable to Data Valid | | 8 | | 10 | | 12 | | 15 | | 15 | ns |
| t _{OLZ} [†] | Output Enable to Output in Low Z | 0 | | 0 | | 0 | | 0 | | 0 | | ns |
| t _{OHZ} [†] | Output Disable to Output in High Z | | 6 | | 7 | | 9 | | 11 | | 15 | ns |
| t _{RCS} | Read Command Setup Time | 0 | | 0 | | 0 | | 0 | | 0 | | ns |
| t _{RCH} | Read Command Hold Time | 0 | | 0 | | 0 | | 0 | | 0 | | ns |
| t _{PU} [§] | Chip Enable to Power Up Time | 0 | | 0 | | 0 | | 0 | | 0 | | ns |
| t _{PD} [§] | Chip Disable to Power Down Time | | 12 | | 15 | | 20 | | 25 | | 35 | ns |

AC CHARACTERISTICS—READ CYCLE (CONTINUED) $(V_{CC} = 5V \pm 10\%$, All Temperature Ranges)⁽²⁾

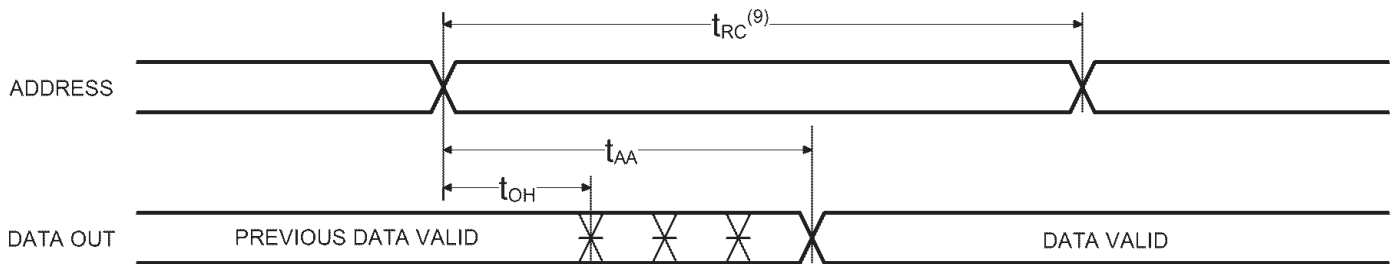
| Sym | Parameter | -45 | | -55 | | -70 | | Unit |
|------------------------------|----------------------------------|-----|-----|-----|-----|-----|-----|------|
| | | Min | Max | Min | Max | Min | Max | |
| t _{RC} | Read Cycle Time | 45 | | 55 | | 70 | | ns |
| t _{AA} | Address Access Time | | 45 | | 55 | | 70 | ns |
| t _{AC} [§] | Chip Enable Access Time | | 45 | | 55 | | 70 | ns |
| t _{OH} | Output Hold from Address Change | 2 | | 2 | | 2 | | ns |
| t _{LZ} [‡] | Chip Enable to Output in Low Z | 2 | | 2 | | 2 | | ns |
| t _{HZ} [†] | Chip Disable to Output in High Z | | 25 | | 25 | | 30 | ns |
| t _{RCS} | Read Command Setup Time | 0 | | 0 | | 0 | | ns |
| t _{RCH} | Read Command Hold Time | 0 | | 0 | | 0 | | ns |
| t _{PU} [§] | Chip Enable to Power Up Time | 0 | | 0 | | 0 | | ns |
| t _{PD} [§] | Chip Disable to Power Down Time | | 45 | | 55 | | 70 | ns |

§ P4C168 only

† P4C170 only

‡ Chip Select/Deselect for P4C169 and P4C170

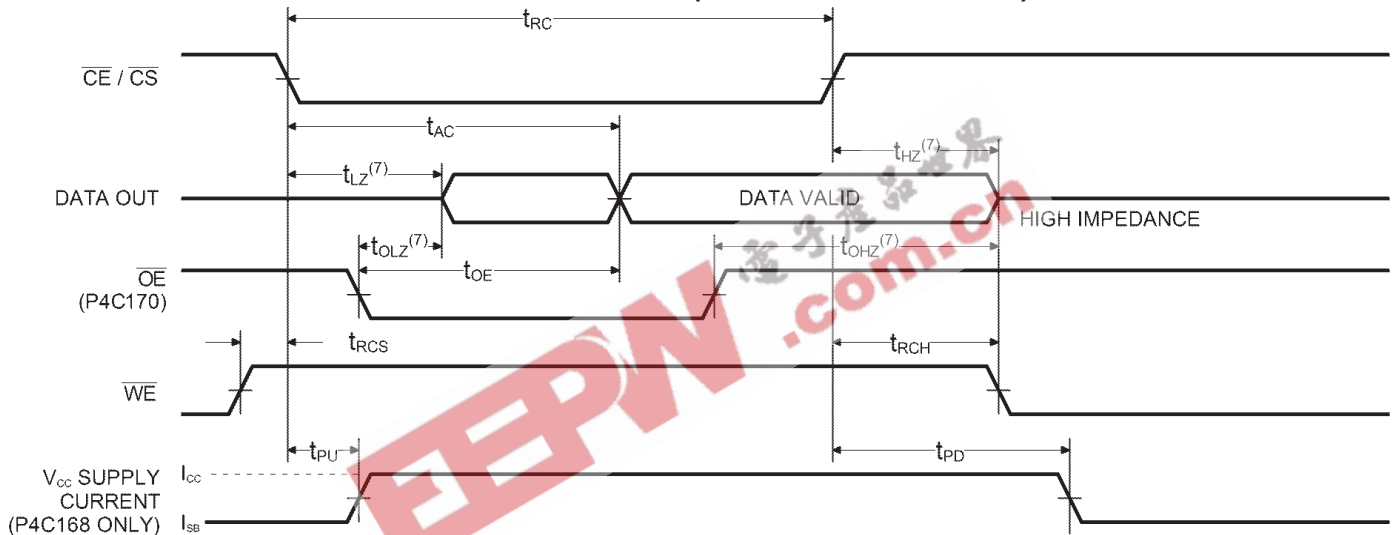
TIMING WAVEFORM OF READ CYCLE NO. 1 (ADDRESS CONTROLLED)^(5,6)



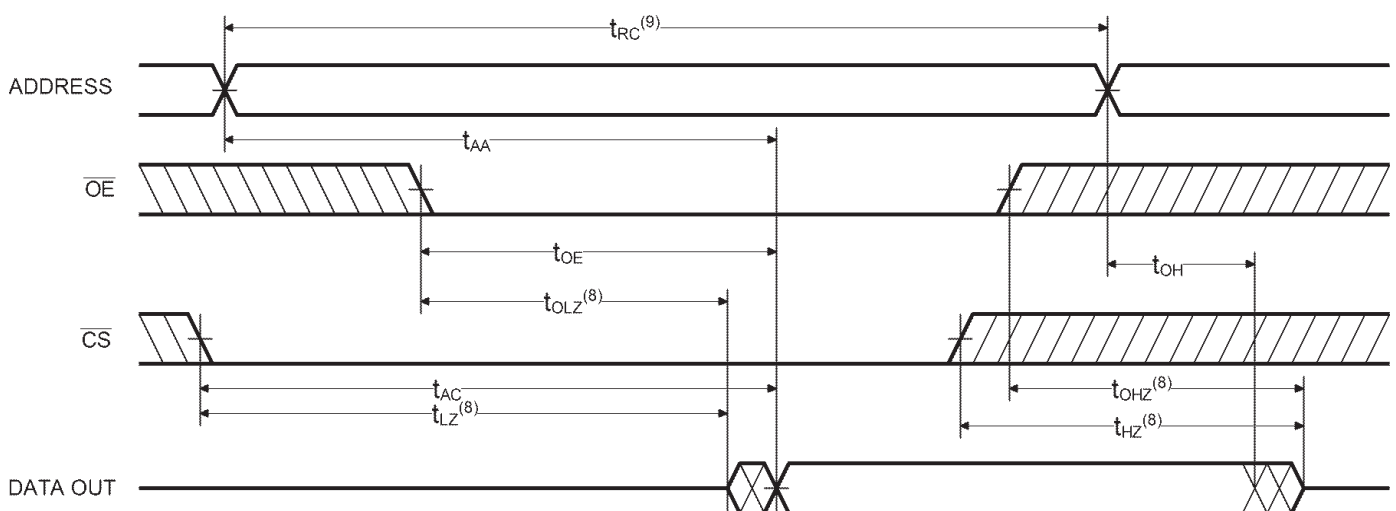
Notes:

- 5. \overline{WE} is HIGH for READ cycle.
- 6. $\overline{CE}/\overline{CS}$ and \overline{OE} are LOW for READ cycle.

TIMING WAVEFORM OF READ CYCLE NO. 2 ($\overline{CE}/\overline{CS}$ CONTROLLED)^(5,7)



TIMING WAVEFORM OF READ CYCLE NO. 3—P4C170 ONLY (\overline{OE} CONTROLLED)⁽⁵⁾



Notes:

- 7. ADDRESS must be valid prior to, or coincident with $\overline{CE}/\overline{CS}$ transition low. For Fast \overline{CS} , t_{AA} must still be met.
- 8. Transition is measured $\pm 200\text{mV}$ from steady state voltage prior to change, with loading as specified in Figure 1.
- 9. Read Cycle Time is measured from the last valid address to the first transitioning address.

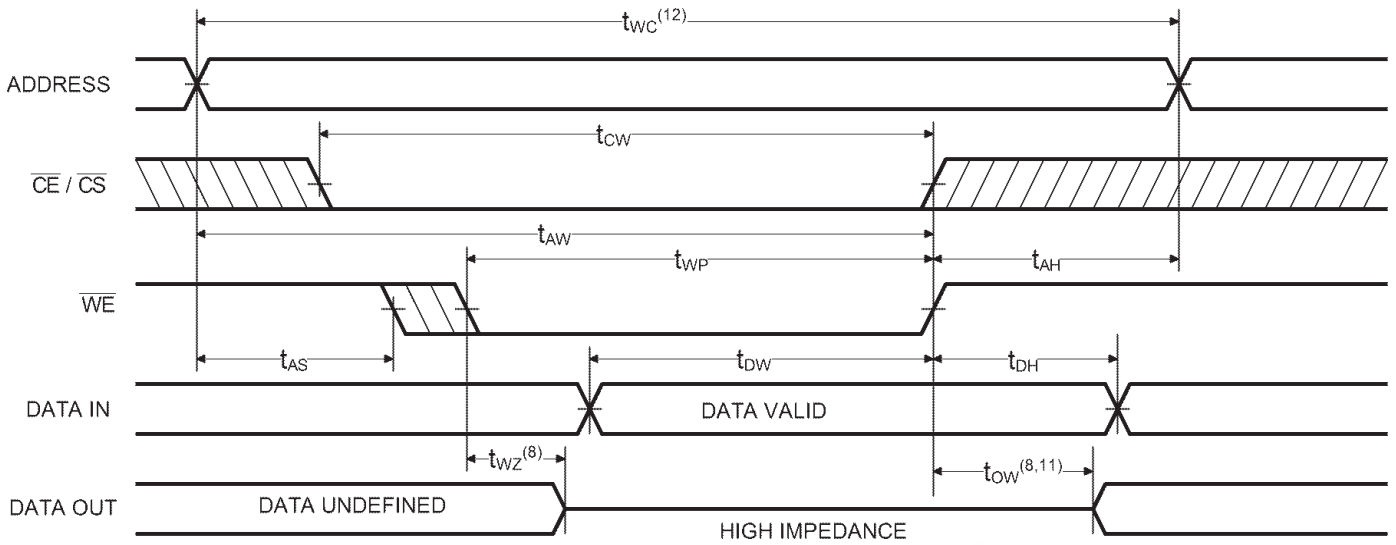
AC ELECTRICAL CHARACTERISTICS - WRITE CYCLE $(V_{CC} = 5V \pm 10\%, \text{ All Temperature Ranges})^{(2)}$

| Sym | Parameter | -12 | | -15 | | -20 | | -25 | | -35 | | Unit |
|-----------------|----------------------------------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | |
| t _{WC} | Write Cycle Time | 12 | | 15 | | 18 | | 20 | | 30 | | ns |
| t _{cw} | Chip Enable Time to End of Write | 12 | | 15 | | 18 | | 20 | | 30 | | ns |
| t _{AW} | Address Valid to End of Write | 12 | | 15 | | 18 | | 20 | | 30 | | ns |
| t _{AS} | Address Set-up Time | 0 | | 0 | | 0 | | 0 | | 0 | | ns |
| t _{WP} | Write Pulse Width | 12 | | 15 | | 18 | | 20 | | 30 | | ns |
| t _{AH} | Address Hold Time | 0 | | 0 | | 0 | | 0 | | 0 | | ns |
| t _{DW} | Data Valid to End of Write | 7 | | 8 | | 10 | | 10 | | 15 | | ns |
| t _{DH} | Data Hold Time | 0 | | 0 | | 0 | | 0 | | 0 | | ns |
| t _{WZ} | Write Enable to Output in High Z | | 4 | | 5 | | 6 | | 7 | | 13 | ns |
| t _{OW} | Output Active from End of Write | 0 | | 0 | | 0 | | 0 | | 0 | | ns |

AC ELECTRICAL CHARACTERISTICS - WRITE CYCLE (CONTINUED) $(V_{CC} = 5V \pm 10\%, \text{ All Temperature Ranges})^{(2)}$

| Sym | Parameter | -45 | | -55 | | -70 | | Unit |
|-----------------|----------------------------------|-----|-----|-----|-----|-----|-----|------|
| | | Min | Max | Min | Max | Min | Max | |
| t _{WC} | Write Cycle Time | 45 | | 55 | | 70 | | ns |
| t _{cw} | Chip Enable Time to End of Write | 40 | | 50 | | 60 | | ns |
| t _{AW} | Address Valid to End of Write | 40 | | 50 | | 60 | | ns |
| t _{AS} | Address Set-up Time | 0 | | 0 | | 0 | | ns |
| t _{WP} | Write Pulse Width | 40 | | 50 | | 60 | | ns |
| t _{AH} | Address Hold Time | 0 | | 0 | | 0 | | ns |
| t _{DW} | Data Valid to End of Write | 20 | | 20 | | 25 | | ns |
| t _{DH} | Data Hold Time | 3 | | 3 | | 3 | | ns |
| t _{WZ} | Write Enable to Output in High Z | | 20 | | 25 | | 30 | ns |
| t _{OW} | Output Active from End of Write | 0 | | 0 | | 0 | | ns |

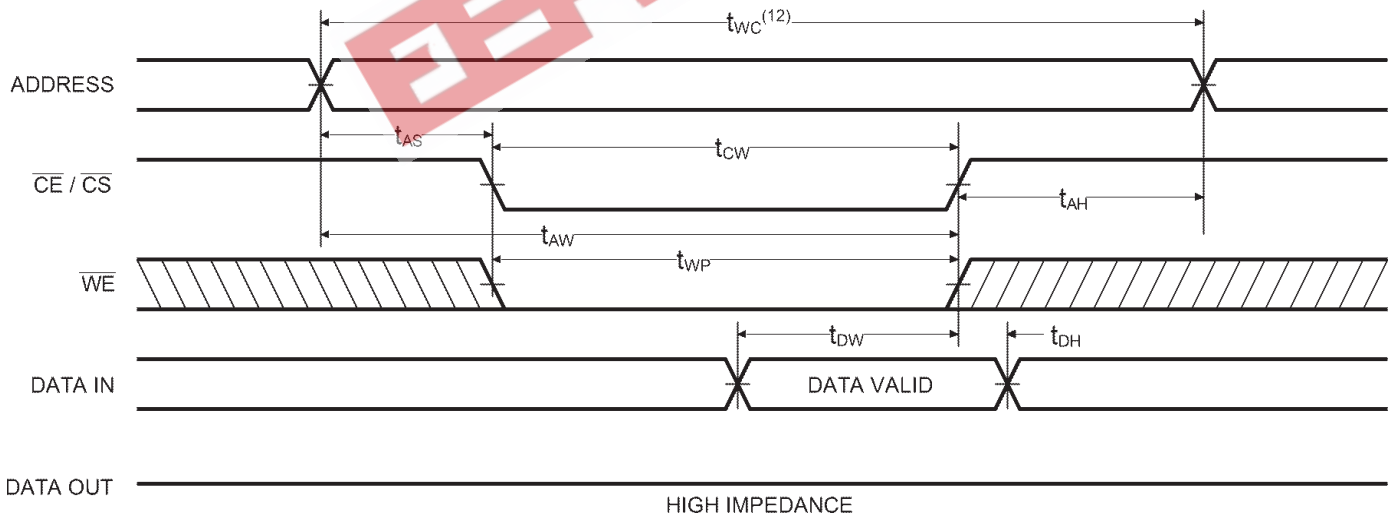
TIMING WAVEFORM OF WRITE CYCLE NO. 1 (\overline{WE} CONTROLLED)⁽¹⁰⁾



Notes:

- 10. $\overline{CE}/\overline{CS}$ and \overline{WE} must be LOW for WRITE cycle.
- 11. If $\overline{CE}/\overline{CS}$ goes HIGH simultaneously with \overline{WE} HIGH, the output remains in a high impedance state.
- 12. Write Cycle Time is measured from the last valid address to the first transitioning address.

TIMING WAVEFORM OF WRITE CYCLE NO. 2 ($\overline{CE}/\overline{CS}$ CONTROLLED)⁽¹⁰⁾



TRUTH TABLES

P4C168 (P4C169)

| Mode | \overline{CE} (\overline{CS}) | \overline{WE} | Output |
|--------------------|-------------------------------------|-----------------|-----------|
| Standby (Deselect) | H | X | High Z |
| Read | L | H | D_{OUT} |
| Write | L | L | High Z |

P4C170

| Mode | \overline{CE} | \overline{WE} | \overline{OE} | Output |
|----------------|-----------------|-----------------|-----------------|-----------|
| Deselect | H | X | X | High Z |
| Read | L | H | L | D_{OUT} |
| Output Inhibit | L | H | H | High Z |
| Write | L | L | X | High Z |

AC TEST CONDITIONS

| | |
|-------------------------------|---------------------|
| Input Pulse Levels | GND to 3.0V |
| Input Rise and Fall Times | 3ns |
| Input Timing Reference Level | 1.5V |
| Output Timing Reference Level | 1.5V |
| Output Load | See Figures 1 and 2 |

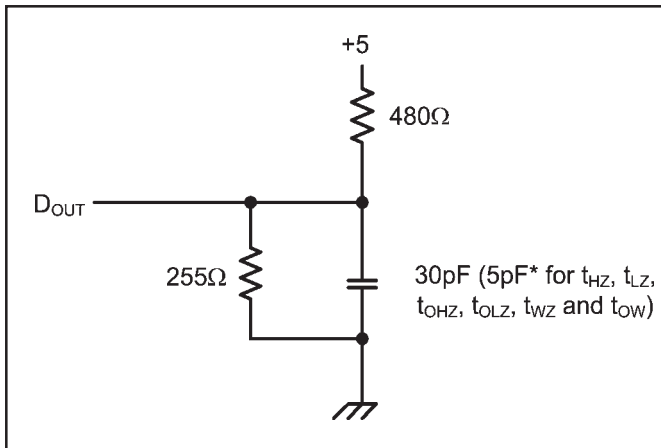


Figure 1. Output Load

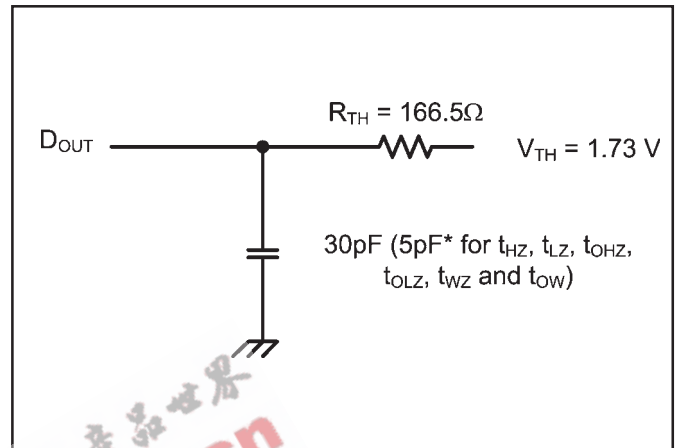


Figure 2. Thevenin Equivalent

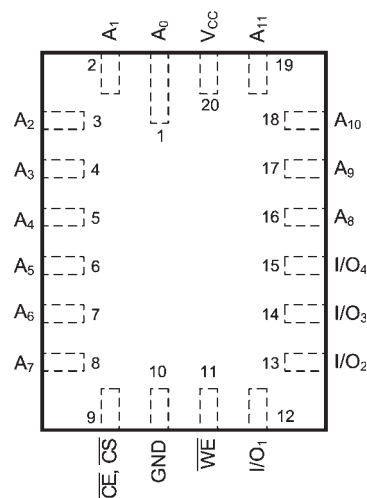
* including scope and test fixture.

Note:

Because of the ultra-high speed of the P4C168, P4C169 AND P4C170 care must be taken when testing these devices; an inadequate setup can cause a normal functioning part to be rejected as faulty. Long high-inductance leads that cause supply bounce must be avoided by bringing the V_{CC} and ground planes directly up to the contactor fingers. A high frequency capacitor of 0.01 μF is also required between V_{CC} and ground.

To avoid signal reflections, proper termination must be used; for example, a 50Ω test environment should be terminated into a 50Ω load with 1.73V (Thevenin Voltage) at the comparator input, and a 116Ω resistor must be used in series with D_{OUT} to match 166Ω (Thevenin Resistance).

LCC PIN CONFIGURATION



LCC (L9)

**ORDERING INFORMATION**

P4C168
P4C169
P4C170

| Device Type | Speed | Package | Processing | |
|-------------|-------|---------|------------|---|
| | | | | C 0°C to +70°C |
| | | | | M -55°C to +125°C |
| | | | | MB Mil Temp. with MIL-STD-883 Class B Compliance |
| | | | | C Ceramic Side Brazed DIP, 300 mil |
| | | | | D Ceramic DIP (CERDIP), 300 mil |
| | | | | F CERPACK |
| | | | | FS Solder Seal Flat Pack |
| | | | | J Plastic SOJ, 300 mil |
| | | | | L Ceramic LCC (290 x 430 mil) |
| | | | | P Plastic DIP, 300 mil |
| | | | | S Plastic SOIC, 300 mil |
| | | | | 12, 15, 20, 25, 35, 45, 55, 70 |
| | | | | 4K x 4 SRAM |

SELECTION GUIDE

The P4C168, P4C169 and P4C170 are available in the following temperature, speed and package options.

| Temperature Range | Package | Speed | | | | |
|------------------------------------|-----------------------|-------|---------|---------|---------|---------|
| | | 12 | 15 | 20 | 25 | 35 |
| Commercial Temperature | Plastic DIP | -12PC | -15PC | -20PC | -25PC | N/A |
| | Plastic SOIC† | -12SC | -15SC | -20SC | -25SC | N/A |
| | Plastic SOJ†† | -12JC | -15JC | -20JC | -25JC | N/A |
| Military Temperature (P4C168 only) | LCC | N/A | -15LM | -20LM | -25LM | -35LM |
| | CERDIP | N/A | -15DM | -20DM | -25DM | -35DM |
| | Side Brazed DIP | N/A | -15CM | -20CM | -25CM | -35CM |
| | CERPACK | N/A | -15FM | -20FM | -25FM | -35FM |
| | Solder Seal Flat Pack | N/A | -15FSM | -20FSM | -25FSM | -35FSM |
| Military Processed* (P4C168 only) | LCC | N/A | -15LMB | -20LMB | -25LMB | -35LMB |
| | CERDIP | N/A | -15DMB | -20DMB | -25DMB | -35DMB |
| | Side Brazed DIP | N/A | -15CMB | -20CMB | -25CMB | -35CMB |
| | CERPACK | N/A | -15FMB | -20FMB | -25FMB | -35FMB |
| | Solder Seal Flat Pack | N/A | -15FSMB | -20FSMB | -25FSMB | -35FSMB |

† P4C168 and P4C169 only.

†† P4C168

* Military temperature range with MIL-STD-883, Class B processing.

N/A = Not available

SELECTION GUIDE (CONTINUED)

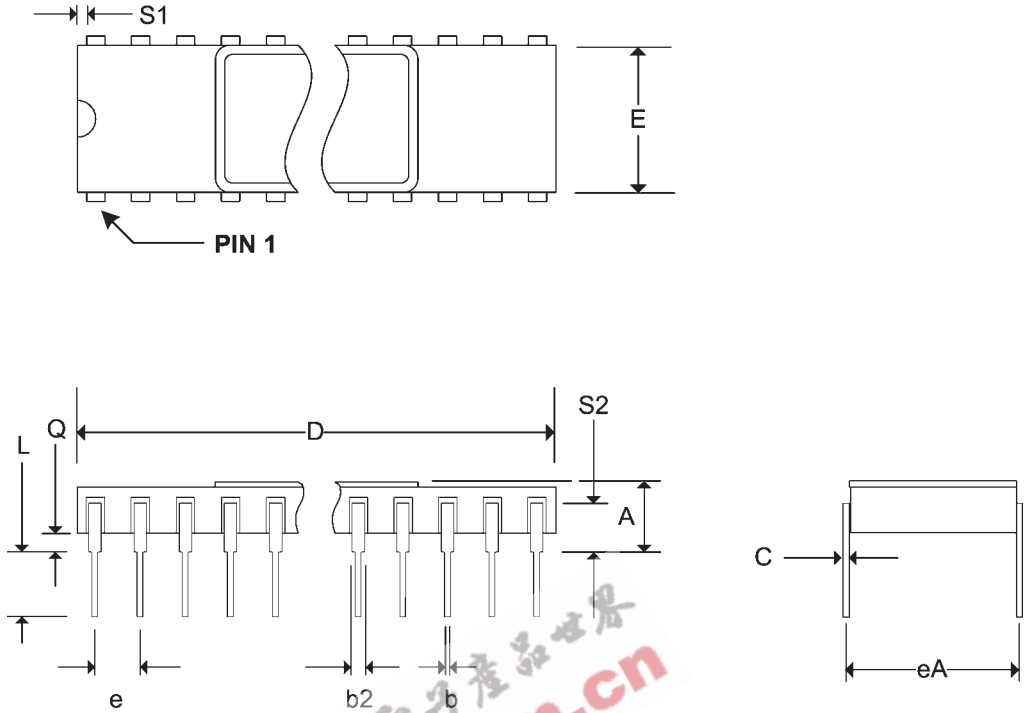
| Temperature Range | Package | Speed | | |
|---------------------------------------|-----------------------|---------|---------|---------|
| | | 45 | 55 | 70 |
| Military Temperature (P4C168 only) | LCC | -45LM | -55LM | -70LM |
| | CERDIP | -45DM | -55DM | -70DM |
| | Side Brazed DIP | -45CM | -55CM | -70CM |
| | CERPACK | -45FM | -55FM | -70FM |
| | Solder Seal Flat Pack | -45FSM | -55FSM | -70FSM |
| Military Processed* (P4C168 only) | LCC | -45LMB | -55LMB | -70LMB |
| | CERDIP | -45DMB | -55DMB | -70DMB |
| | Side Brazed DIP | -45CMB | -55CMB | -70CMB |
| | CERPACK | -45FMB | -55FMB | -70FMB |
| | Solder Seal Flat Pack | -55FSMB | -55FSMB | -70FSMB |

* Military temperature range with MIL-STD-883, Class B processing.

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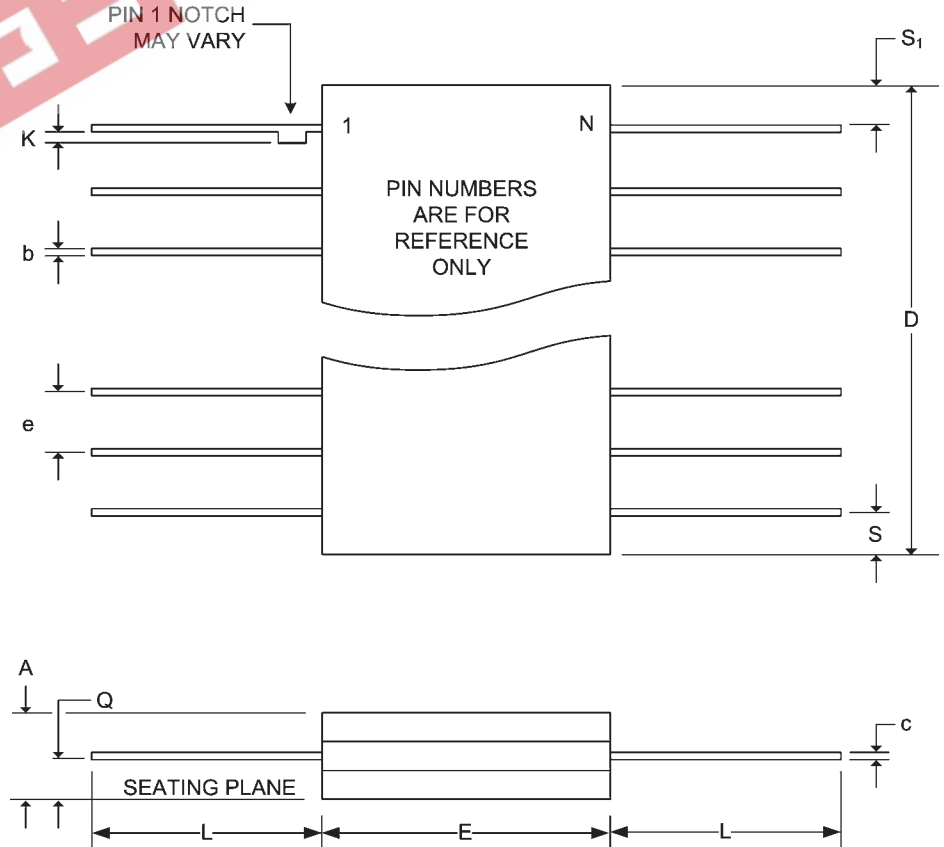
| Pkg # | C6 | |
|--------|--------------|-------|
| # Pins | 20 (300 mil) | |
| Symbol | Min | Max |
| A | - | 0.200 |
| b | 0.014 | 0.026 |
| b2 | 0.045 | 0.065 |
| C | 0.008 | 0.018 |
| D | - | 1.060 |
| E | 0.220 | 0.310 |
| eA | 0.300 BSC | |
| e | 0.100 BSC | |
| L | 0.125 | 0.200 |
| Q | 0.015 | 0.070 |
| S1 | 0.005 | - |
| S2 | 0.005 | - |

SIDE BRAZED DUAL IN-LINE PACKAGE



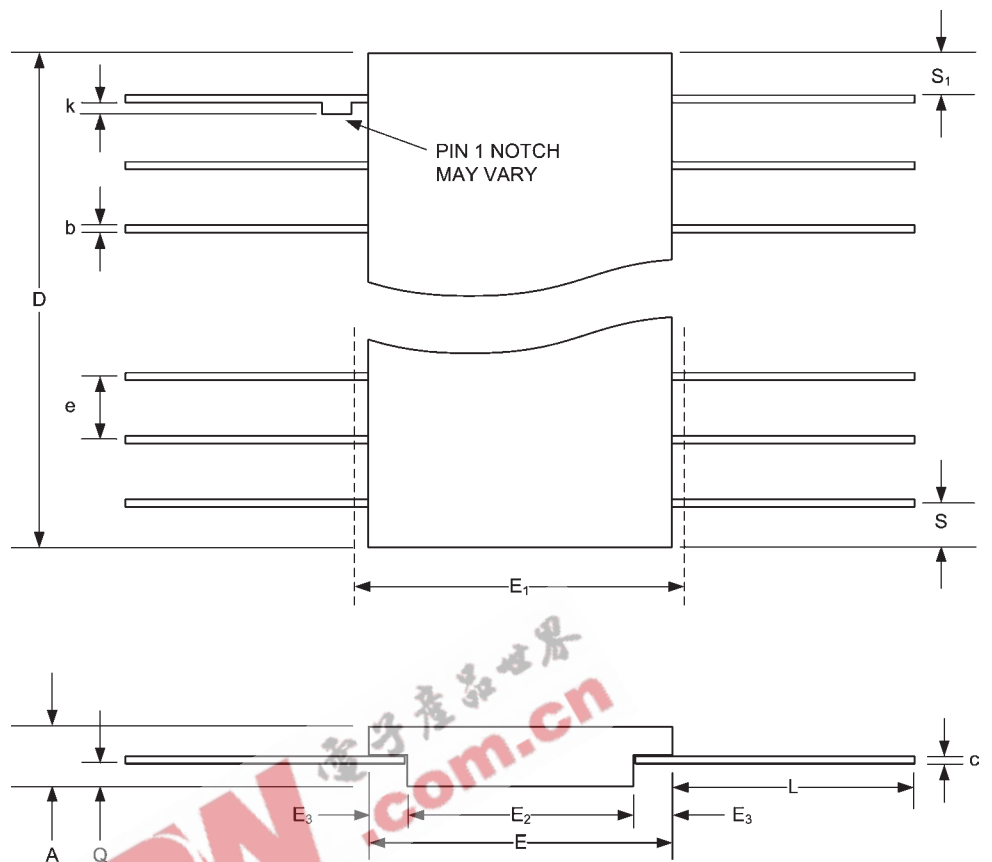
| Pkg # | F2 | |
|--------|-----------|-------|
| # Pins | 20 | |
| Symbol | Min | Max |
| A | 0.060 | 0.090 |
| b | 0.015 | 0.022 |
| c | 0.004 | 0.009 |
| D | - | 0.530 |
| E | 0.305 | 0.355 |
| e | 0.050 BSC | |
| k | 0.005 | 0.018 |
| L | 0.250 | 0.370 |
| Q | 0.026 | 0.045 |
| S | - | 0.085 |
| S1 | 0.005 | - |

CERPACK CERAMIC FLAT PACKAGE



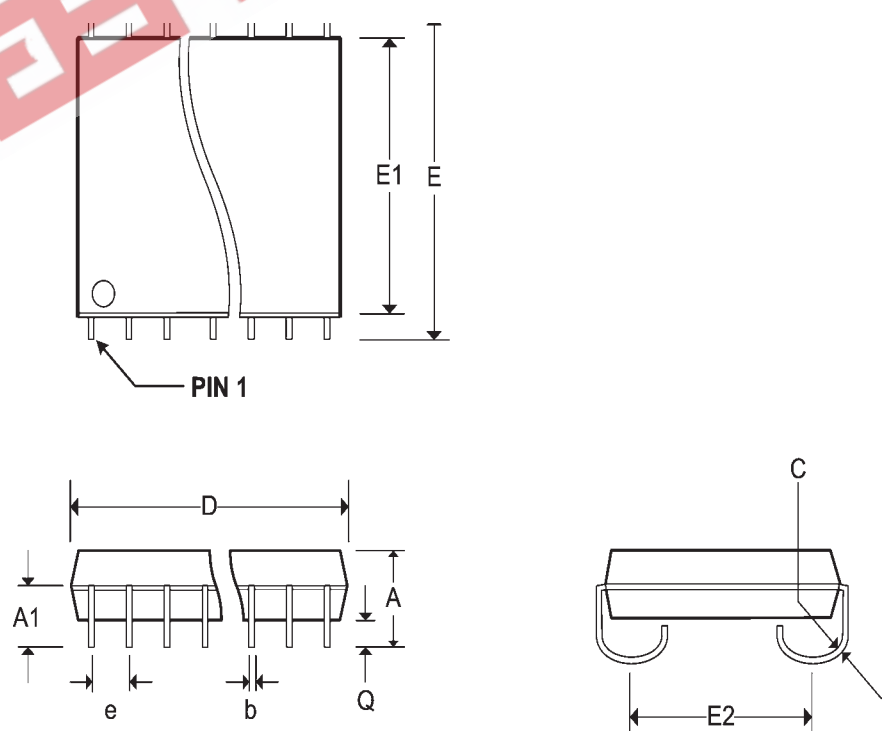
| | | |
|--------|-------------|------------|
| Pkg # | FS-2 | |
| # Pins | 20 | |
| Symbol | Min | Max |
| A | 0.045 | 0.115 |
| b | 0.015 | 0.022 |
| b1 | 0.015 | 0.019 |
| c | 0.004 | 0.009 |
| c1 | 0.004 | 0.006 |
| D | - | 0.540 |
| E | 0.245 | 0.300 |
| E1 | - | 0.330 |
| E2 | 0.130 | - |
| E3 | 0.030 | - |
| e | 0.050 BSC | |
| k | 0.008 | 0.015 |
| L | 0.250 | 0.370 |
| Q | 0.026 | 0.045 |
| S1 | 0.000 | - |
| M | - | 0.0015 |
| N | 20 | |

SOLDER SEAL FLAT PACKAGE



| | | |
|--------|--------------|------------|
| Pkg # | J2 | |
| # Pins | 20 (300 mil) | |
| Symbol | Min | Max |
| A | 0.120 | 0.140 |
| A1 | 0.080 | - |
| b | 0.014 | 0.020 |
| C | 0.008 | 0.013 |
| D | 0.496 | 0.512 |
| e | 0.050 BSC | |
| E | 0.335 | 0.347 |
| E1 | 0.292 | 0.300 |
| E2 | 0.267 BSC | |
| Q | 0.025 | - |

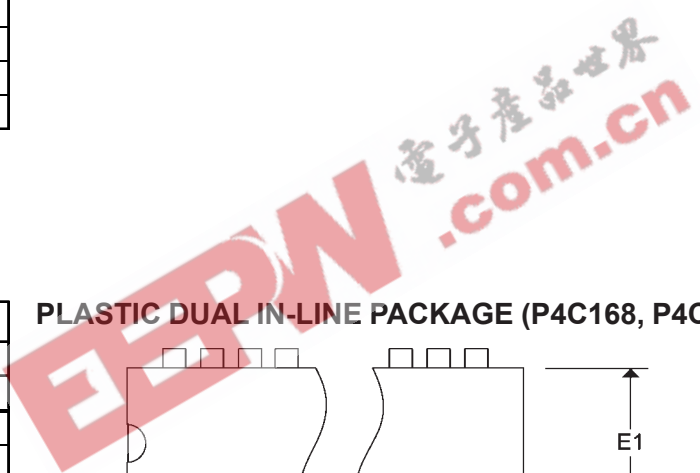
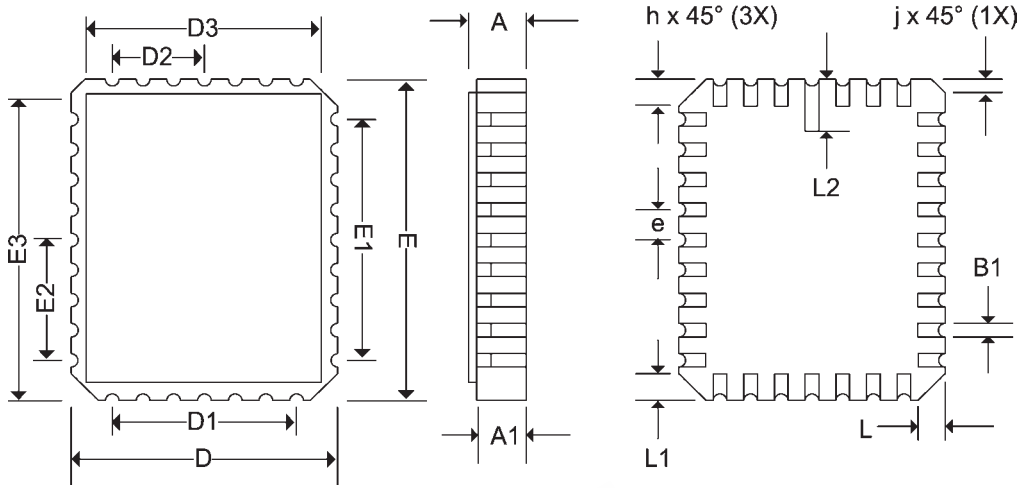
SOJ SMALL OUTLINE IC PACKAGE





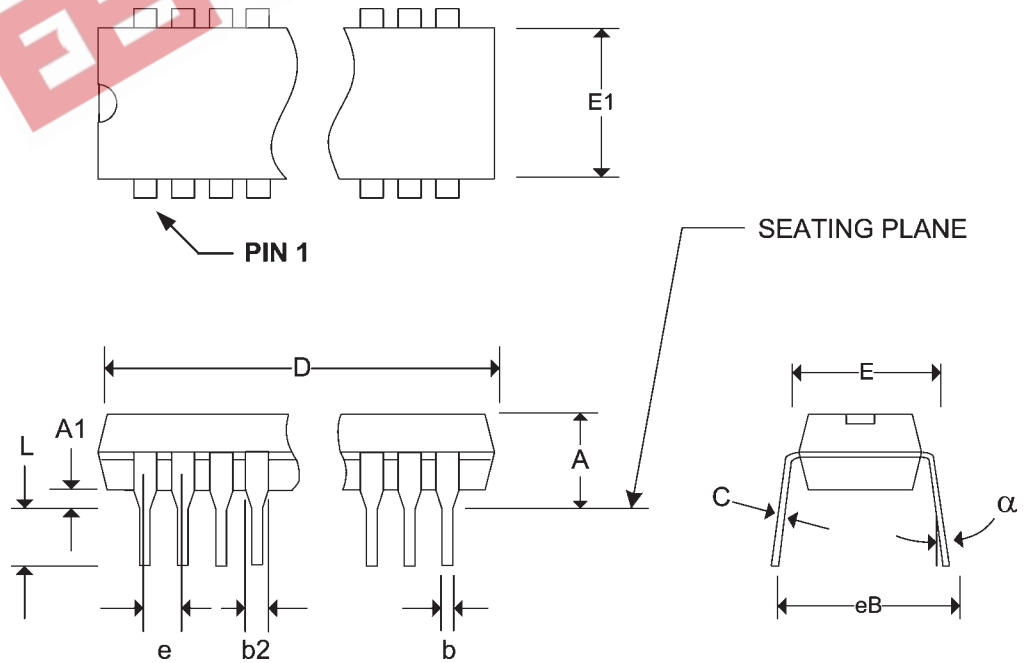
| | | |
|--------|------------|------------|
| Pkg # | L9 | |
| # Pins | 20 | |
| Symbol | Min | Max |
| A | 0.060 | 0.075 |
| A1 | 0.050 | 0.066 |
| B1 | 0.022 | 0.028 |
| D | 0.280 | 0.305 |
| D1 | 0.150 BSC | |
| D2 | 0.075 BSC | |
| D3 | - | 0.305 |
| E | 0.420 | 0.440 |
| E1 | 0.250 BSC | |
| E2 | 0.125 BSC | |
| E3 | - | 0.440 |
| e | 0.050 BSC | |
| h | 0.020 REF | |
| j | 0.010 REF | |
| L | 0.045 | 0.055 |
| L1 | 0.045 | 0.055 |
| L2 | 0.075 | 0.098 |
| ND | 4 | |
| NE | 6 | |

RECTANGULAR LEADLESS CHIP CARRIER



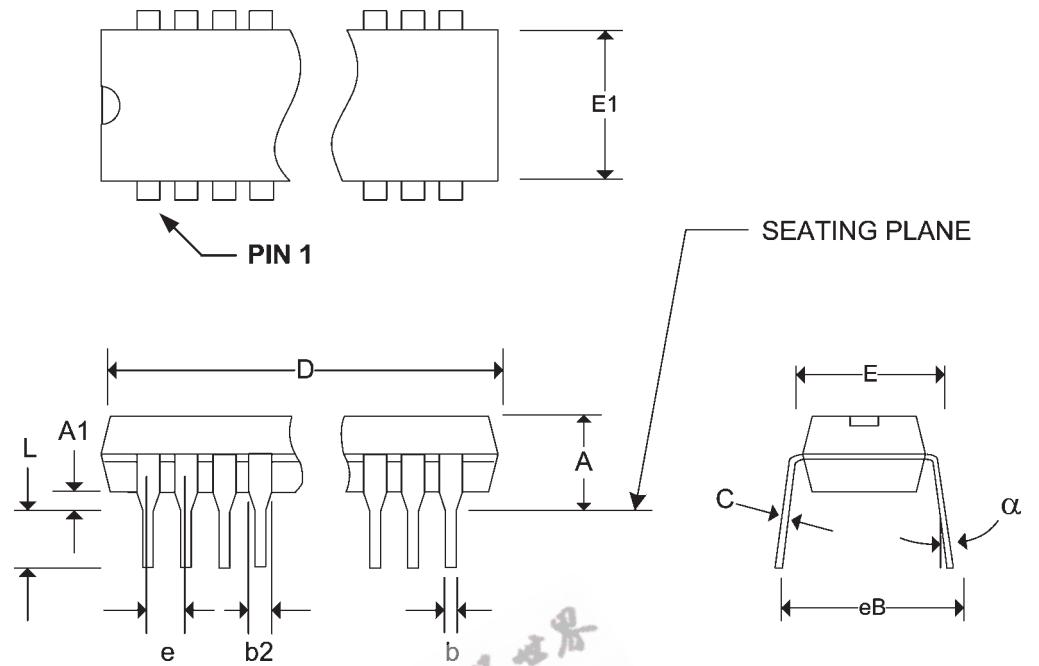
| | | |
|--------|--------------|------------|
| Pkg # | P2 | |
| # Pins | 20 (300 mil) | |
| Symbol | Min | Max |
| A | - | 0.210 |
| A1 | 0.015 | - |
| b | 0.014 | 0.022 |
| b2 | 0.045 | 0.070 |
| C | 0.008 | 0.014 |
| D | 0.980 | 1.060 |
| E1 | 0.240 | 0.280 |
| E | 0.300 | 0.325 |
| e | 0.100 BSC | |
| eB | - | 0.430 |
| L | 0.115 | 0.150 |
| α | 0° | 15° |

PLASTIC DUAL IN-LINE PACKAGE (P4C168, P4C169)



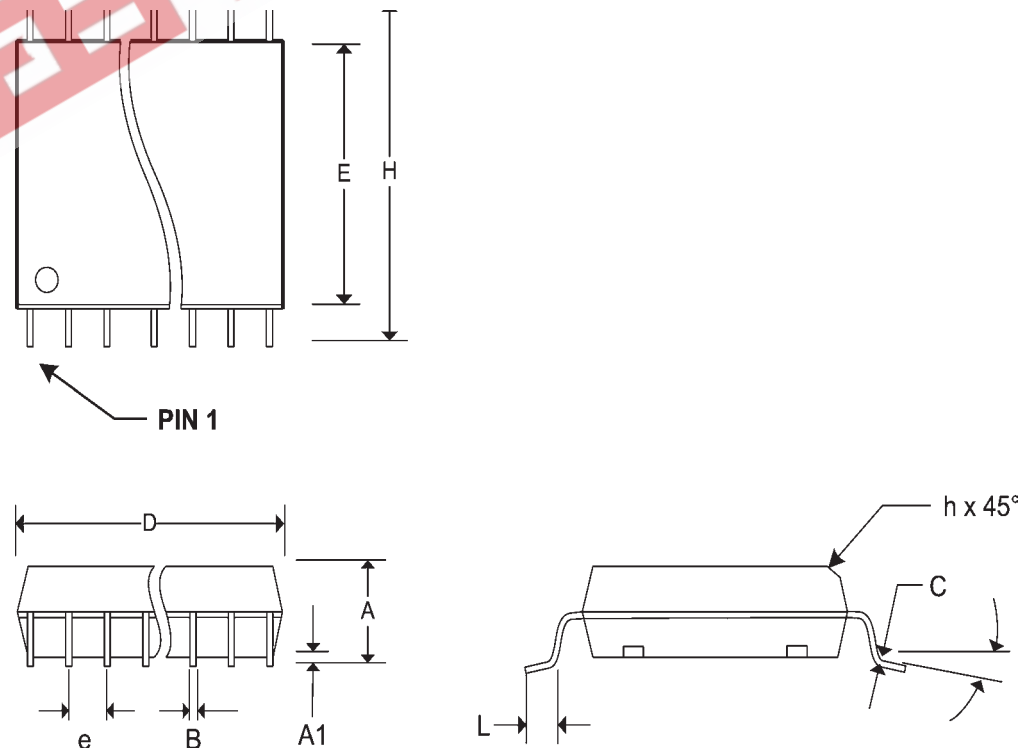
| Pkg # | P3 | |
|----------|--------------|-------|
| # Pins | 22 (300 Mil) | |
| Symbol | Min | Max |
| A | - | 0.210 |
| A1 | 0.015 | - |
| b | 0.014 | 0.022 |
| b2 | 0.045 | 0.070 |
| C | 0.008 | 0.014 |
| D | 1.145 | 1.165 |
| E1 | 0.240 | 0.280 |
| E | 0.300 | 0.325 |
| e | 0.100 BSC | |
| eB | - | 0.430 |
| L | 0.115 | 0.150 |
| α | 0° | 15° |

PLASTIC DUAL IN-LINE PACKAGE (P4C170)



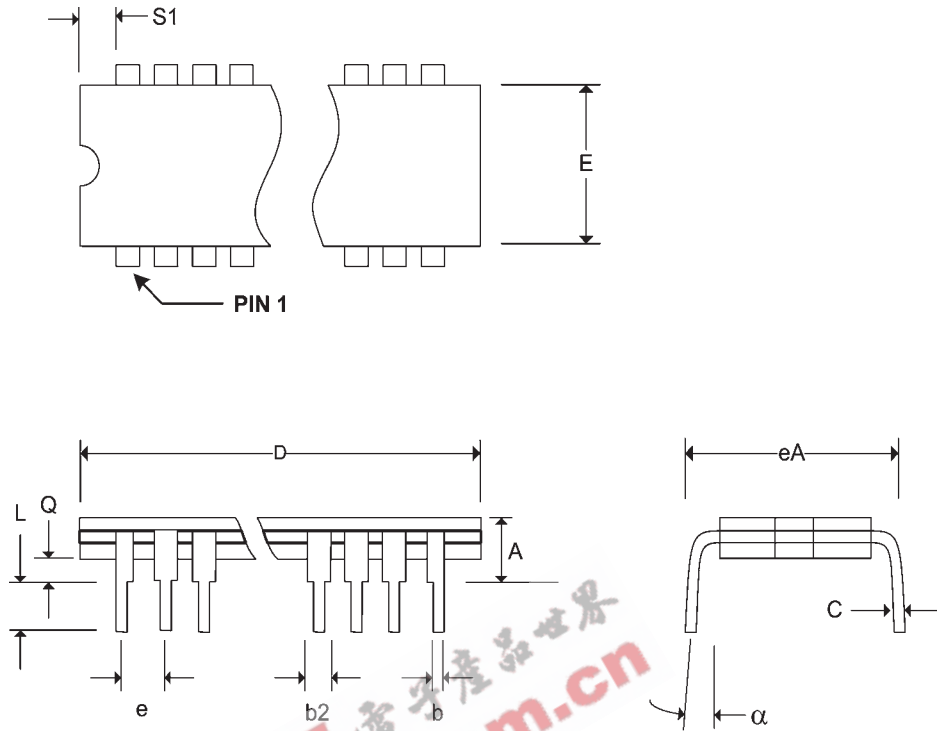
| Pkg # | S2 | |
|----------|--------------|-------|
| # Pins | 20 (300 mil) | |
| Symbol | Min | Max |
| A | 0.093 | 0.104 |
| A1 | 0.004 | 0.012 |
| b2 | 0.013 | 0.020 |
| C | 0.009 | 0.012 |
| D | 0.496 | 0.511 |
| e | 0.050 BSC | |
| E | 0.291 | 0.299 |
| H | 0.394 | 0.419 |
| h | 0.010 | 0.029 |
| L | 0.016 | 0.050 |
| α | 0° | 8° |

SOIC/SOP SMALL OUTLINE IC PACKAGE



| Pkg # | D2 | |
|----------|--------------|-------|
| # Pins | 20 (300 mil) | |
| Symbol | Min | Max |
| A | - | 0.200 |
| b | 0.014 | 0.026 |
| b2 | 0.045 | 0.065 |
| C | 0.008 | 0.018 |
| D | - | 1.060 |
| E | 0.220 | 0.310 |
| eA | 0.300 BSC | |
| e | 0.100 BSC | |
| L | 0.125 | 0.200 |
| Q | 0.015 | 0.070 |
| S1 | 0.005 | - |
| α | 0° | 15° |

CERDIP DUAL IN-LINE PACKAGE



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